

FLAT-TYPE CAPACITOR FOR INTEGRATED CIRCUIT AND METHOD OF  
MANUFACTURING THE SAME

ABSTRACT OF THE DISCLOSURE

5           Embodiments of the invention provide flat-type capacitors that prevent degradation of  
the dielectric layer, thereby improving the electrical properties of the capacitor. The  
capacitor includes a lower interconnection formed in a predetermined portion of a  
semiconductor substrate, a lower electrode formed on the lower interconnection that is  
electrically coupled to the lower interconnection; a concave dielectric layer formed on the  
10 lower electrode; a concave upper electrode formed on the dielectric layer; a first upper  
interconnection that is electrically coupled to the lower interconnection; and a second upper  
interconnection that is coupled to the upper electrode. The concave upper electrode is larger  
than the lower electrode.